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# AZ N6000 Product Summary

**Process capability:**

- 0.9µm CD @ 2.0 µm FT
- 1.10µm CD @ 3.5 µm FT
- 1.30µm CD @ 7.0 µm FT

**AZ N6020:** For 2.0 µm FT, DTP = 64 mJ/cm²

**AZ N6035:** For 3.5 µm FT, DTP = 60 mJ/cm²

**AZ N6070:** For 7.0 µm FT, DTP = 114 mJ/cm²
AZ N6000 Photoresist
Spin Speed Curve

AZ N6000 Photoresist series

Film Thickness (Å)

RPM’s

AZ N6010
AZ N6020
AZ N6035
AZ N6070
AZ N6010 Photoresist

Processing

Film Thickness: 1.0µm
Softbake: 90°C for 60 sec - proximity
Exposure: Nikon 0.54NA stepper
PEB: 110°C for 60 sec - contact mode
Develop: AZ 300 MIF Developer,
Single puddle for 60-120 sec. @ 23°C

Analysis

Hitachi S-4000 SEM: SEM pictures at 75° tilt.
CD’s measured at top of resist profile
AZ N6010 Photoresist
Resolution Dense Lines @ 50 mJ/cm²

FT: 1.0µm
SB: 90°C/60 sec - proximity
Nikon 0.54NA i-line stepper
PEB: 110°C / 60 sec - contact mode
AZ 300 MIF Developer, Single puddle for 60-120 sec. @ 23°C
AZ N6010 Photoresist
DOF 0.7µm Dense Lines @ 50 mJ/cm²

F=-0.8  F=-0.6  F=-0.4  F=-0.2  F=0.0

F=0.2

F=1.2  F=1.0  F=0.8  F=0.6  F=0.4

FT: 1.0µm
SB: 90°C/60 sec – proximity, Nikon 0.54NA i-line stepper
PEB: 110°C / 60sec - contact mode
AZ 300 MIF Developer, Single puddle for 60-120 sec. @ 23°C
AZ N6020 Photoresist

Processing

**Film Thickness:** 2.017µm at Emin  
**Softbake:** 110°C for 60 sec - contact  
**Exposure:** ASML/250, 0.60NA stepper  
**PEB:** 110°C for 60 sec - contact mode  
**Develop:** AZ 300 MIF Developer,  

generate puddle for 60-120 sec. @ 23°C **Analysis**

Hitachi S-4000 SEM: SEM pictures at 75° tilt.  
CD's measured at top of resist profile
AZ N6020 Photoresist

Exposure Latitude of 1.0 µm Isolated Trench

<table>
<thead>
<tr>
<th>Exposure (mJ/cm²)</th>
<th>Image</th>
</tr>
</thead>
<tbody>
<tr>
<td>40</td>
<td>![Image]</td>
</tr>
<tr>
<td>43</td>
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<tr>
<td>64</td>
<td>![Image]</td>
</tr>
<tr>
<td>67</td>
<td>![Image]</td>
</tr>
</tbody>
</table>

± 18.3% Exposure Latitude

**Best focus, F = 0.4 µm**

FT: 2.017µm at Emin

SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper

PEB: 110°C/ 60 sec - contact mode

AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Isolated Trench

± 18.3% Exposure Latitude

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude at 1.0µm Isolated Trench

$F = 0.2 \mu m$

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Exposure Latitude at 1.0µm Isolated Trench

FT: 2.017µm at Emin
SB: 110°C/60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Exposure Latitude at 1.0µm Isolated Trench

\[ F = -0.2 \, \mu m \]

FT: 2.017µm at Emin
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Exposure Latitude at 1.0µm Isolated Trench

FT: 2.017µm at Emín
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 μm Isolated Trench

E = 55 mJ/cm²

F = 1.2
FT: 2.017μm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist

DOF of 1.0 µm Isolated Trench

E = 61 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Isolated Trench

FT: 2.017 µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution of Isolated Trench

1.0 µm

0.90 µm

0.80 µm

0.75 µm

FT: 2.017µm at Emin
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Resolution of Isolated Trench

FT: 2.017 µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution of Isolated Trench

E = 55 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

± 25.4 % Exposure Latitude
Best focus, \( F = 0.4 \mu m \)

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines
± 25.4 % Exposure Latitude

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

FT:  2.017µm at Emin
SB:  110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

40 mJ/cm² 43 mJ/cm² 46 mJ/cm² 49 mJ/cm² 52 mJ/cm²

F = 0.0 µm

70 mJ/cm² 67 mJ/cm² 64 mJ/cm² 61 mJ/cm² 58 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

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<td><img src="image9.png" alt="Image" /></td>
</tr>
<tr>
<td>70</td>
<td><img src="image10.png" alt="Image" /></td>
</tr>
</tbody>
</table>

\[ F = -0.2 \mu m \]

FT: 2.017µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec – contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

FT: 2.017 µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Dense Lines

F = 1.2  F = 0.8  F = 0.0  F = 0.2

F = -0.6  F = -0.4  F = -0.2  F = 0.4

E = 55 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Dense Lines

E = 61 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Dense lines

(measurement at the line’s top and bottom)

FT: 2.017µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution of Dense Lines

1.0 µm  0.90 µm  0.80 µm  0.75 µm

FT: 2.017µm at Emin
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution of Dense Lines

FT: 2.017 µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Resolution of Isolated Trench and Dense Lines

FT: 2.017µm at Emin  Nominal Linewidth [µm]
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution of Dense Lines

E = 55 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist

Resolution of Isolated Trench and Dense Lines

FT: 2.017µm at Emin
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

AZ N6020 Ultimate Resolution – Dense Lines

E = 40 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

AZ N6020 Ultimate Resolution – Isolated Trench

E = 40 mJ/cm²

FT: 2.017µm at Emin
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

Processing

Film Thickness: 2.067µm at Emax
Softbake: 110°C for 60 sec - contact
Exposure: ASML/250, 0.60NA stepper
PEB: 110°C for 60 sec - contact mode
Develop: AZ 300 MIF Developer,
Single puddle for 60-120 sec. @ 23°C

Analysis

Hitachi S-4000 SEM: SEM pictures at 75° tilt.
CD’s measured at top of resist profile
AZ N6020 Photoresist

Exposure Latitude of 1.0 µm Isolated Trench

± 22 % Exposure Latitude

Best Focus, $F = 0.4\mu m$

FT: 2.067µm at Emax

SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper

PEB: 110°C/60 sec - contact mode

AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Isolated Trench
± 22 % Exposure Latitude

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Isolated Trench

F = 0.0µm

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

**Exposure Latitude of 1.0µm Isolated Trench**

<table>
<thead>
<tr>
<th>Exposure (mJ/cm²)</th>
<th>Photolithography Result</th>
</tr>
</thead>
<tbody>
<tr>
<td>40</td>
<td><img src="image1.png" alt="Image" /></td>
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<tr>
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<tr>
<td>70</td>
<td><img src="image10.png" alt="Image" /></td>
</tr>
<tr>
<td></td>
<td><strong>F = - 0.2µm</strong></td>
</tr>
</tbody>
</table>

**Parameters**

- **FT**: 2.067µm at Emax
- **SB**: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
- **PEB**: 110°C/60 sec - contact mode
- **AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C**
AZ N6020 Photoresist
Exposure Latitude of 1.0µm Isolated Trench

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Isolated Trench

F = -0.6  F = -0.4  F = -0.2  F = 0.0  F = 0.2

F = 0.4  F = 0.8  F = 1.0  F = 1.2

E = 64 mJ/cm²

FT: 2.067µm at Emax
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 μm Isolated Trench

FT: 2.067μm at Emax
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

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<tr>
<td>73</td>
<td></td>
</tr>
<tr>
<td>76</td>
<td></td>
</tr>
</tbody>
</table>

± 20.8 % Exposure Latitude

**Best Focus, \( F = 0.4\mu m \)**

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

Exposure Latitude of 1.0 µm Dense Lines

± 20.8 % Exposure Latitude

FT: 2.067µm at Emax
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0 µm Dense Lines

40 mJ/cm²  43 mJ/cm²  46 mJ/cm²  49 mJ/cm²  52 mJ/cm²

58 mJ/cm²  61 mJ/cm²  64 mJ/cm²  49 mJ/cm²  55 mJ/cm²

55 mJ/cm²  67 mJ/cm²  64 mJ/cm²  58 mJ/cm²  70 mJ/cm²

$F = 0.0µm$

FT:  2.067µm at Emax
SB:  110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0µm Dense Lines

40 mJ/cm²  43 mJ/cm²  46 mJ/cm²  49 mJ/cm²  52 mJ/cm²

43 mJ/cm²  46 mJ/cm²  49 mJ/cm²  52 mJ/cm²  55 mJ/cm²

F = - 0.2µm

70 mJ/cm²  67 mJ/cm²  64 mJ/cm²  61 mJ/cm²  58 mJ/cm²

FT:  2.067µm at Emax
SB:  110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Exposure Latitude of 1.0µm Dense Lines

FT: 2.067µm at Emax
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
DOF of 1.0 µm Dense Lines

F = -0.6  F = -0.4  F = -0.2  F = 0.0  F = 0.2

E = 64 mJ/cm²

FT: 2.067µm at Emax
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist

Focus Latitude of 1.0 µm Dense Lines

(measurement at the line’s top and bottom)

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Resolution of Isolated Trench

E = 64 mJ/cm²

FT: 2.067µm at Emax
SB: 110°C/60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Resolution Dense Lines

E = 64 mJ/cm²

FT: 2.067 µm at Emax
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist

Resolution of Isolated Trench and Dense Lines

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Ultimate Resolution – Isolated Trench

40 mJ/cm²

43 mJ/cm²

46 mJ/cm²

FT: 2.067µm at Emax
SB: 110°C/60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6020 Photoresist
Ultimate Resolution – Dense Lines

40 mJ/cm²

43 mJ/cm²

46 mJ/cm²

FT: 2.067µm at Emax
SB: 110°C/ 60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist

Post Exposure Bake Sensitivity, 2.0 µm Dense Lines

FT: 2.067µm at Emax
SB: 110°C/ 60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/ 60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C

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AZ N6020 Photoresist
Post Exposure Bake Sensitivity, 2.0 µm Dense Lines

FT: 2.067µm at Emax
SB: 110°C/60 sec - contact
ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 60-120 sec. @ 23°C
AZ N6035 Photoresist

Processing

**Film Thickness:** 3.5 µm  
**Softbake:** 110°C for 60 sec - contact  
**Exposure:** ASML/250, 0.60NA stepper  
**PEB:** 110°C for 60 sec - contact mode  
**Develop:** AZ 300 MIF Developer,  
Single puddle for 120 sec. @ 23°C

Analysis

Hitachi S-4000 SEM: SEM pictures at 75° tilt.  
CD’s measured at top of resist profile
AZ N6035 Photoresist
Resolution Dense Lines

E = 60 mJ/cm²

FT: 3.5µm
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 120 sec. @ 23°C
AZ N6035 Photoresist
DOF of 2.0 µm Dense Lines

F = 1.5  F = 1.2  F = 0.9  F = 0.6  F = 0.3

E = 60 mJ/cm²

FT: 3.5µm
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 120 sec. @ 23°C

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AZ N6070 Photoresist

Processing

**Film Thickness:** 5.0 µm  
**Softbake:** 110°C for 60 sec - contact  
**Exposure:** ASML/250, 0.60NA stepper  
**PEB:** 110°C for 60 sec - contact mode  
**Develop:** AZ 300 MIF Developer,  
Single puddle for 240 sec. @ 23°C

Analysis

Hitachi S-4000 SEM: SEM pictures at 75° tilt.  
CD’s measured at top of resist profile
AZ N6070 Photoresist

Resolution Dense Lines

2.0 µm

1.9 µm

1.8 µm

1.7 µm

1.6 µm

1.5 µm

1.4 µm

1.3 µm

1.2 µm

E = 114 mJ/cm²

FT: 5.0µm

SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper

PEB: 110°C/60 sec - contact mode

AZ 300 MIF Developer, Single puddle 240 sec. @ 23°C
AZ N6070 Photoresist
DOF of 2.0 µm Dense Lines

F = 1.5
F = 1.2
F = 0.9
F = 0.6
F = 0.3

E = 114 mJ/cm²

F = -1.2
F = -0.9
F = -0.6
F = -0.3

FT: 5.0µm
SB: 110°C/60 sec – contact, ASML/250, 0.60NA stepper
PEB: 110°C/60 sec - contact mode
AZ 300 MIF Developer, Single puddle 240 sec. @ 23°C

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